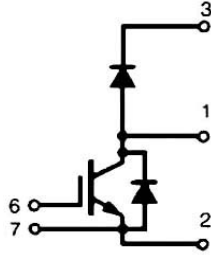
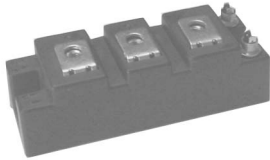
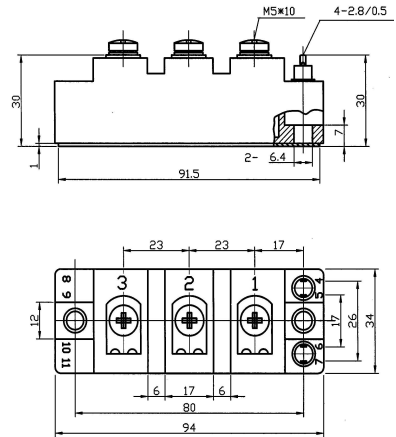


SID75S12

SPT IGBT Modules



Dimensions in mm (1mm = 0.0394")



Absolute Maximum Ratings

$T_c = 25^\circ\text{C}$, unless otherwise specified

| Symbol | Conditions | Values | Units |
|----------------------|---|-----------------------|------------------|
| IGBT | | | |
| V_{CES} | | 1200 | V |
| I_c | $T_c = 25(80)^\circ\text{C}$ | 100(70) | A |
| I_{CRM} | $T_c = 25(80)^\circ\text{C}$, $t_P = 1\text{ms}$ | 200(140) | A |
| V_{GES} | | ± 20 | V |
| $T_{Vj}(T_{stg})$ | $T_{OPERATION} \leq T_{stg}$ | $-40 \dots +150(125)$ | $^\circ\text{C}$ |
| V_{isol} | AC, 1min | 4000 | V |
| Inverse Diode | | | |
| $I_{F=-I_c}$ | $T_c = 25(80)^\circ\text{C}$ | 75(50) | A |
| I_{FRM} | $T_c = 25(80)^\circ\text{C}$, $t_P = 1\text{ms}$ | 200(140) | A |
| I_{FSM} | $t_P = 10\text{ms}$; sin.; $T_j = 150^\circ\text{C}$ | 550 | A |

SID75S12

SPT IGBT Modules

Characteristics

T_c = 25°C, unless otherwise specified

| Symbol | Conditions | min. | typ. | max. | Units |
|--|--|------|----------|------------|-------|
| IGBT | | | | | |
| V _{GE(th)} | V _{GE} = V _{CE} , I _c = 4mA | 4.8 | 5.5 | 6.5 | V |
| I _{CES} | V _{GE} = 0; V _{CE} = V _{CES} ; T _j = 25(125)°C | | 0.1 | 0.3 | mA |
| V _{CE(TO)} | T _j = 25(125)°C | | 1(0.9) | 1.15(1.05) | V |
| r _{CE} | V _{GE} = 20V, T _j = 25(125)°C | | 18(24) | 24(30) | mΩ |
| V _{CE(sat)} | I _c = 50A; V _{GE} = 15V; chip level | | 1.9(2.1) | 2.35(2.55) | V |
| C _{ies} | under following conditions | | 4.5 | | nF |
| C _{oes} | V _{GE} = 0, V _{CE} = 25V, f = 1MHz | | 0.6 | | |
| C _{res} | | | 0.55 | | |
| L _{CE} | | | | 25 | nH |
| R _{CC+EE'} | res., terminal-chip T _c = 25(125)°C | | 0.75(1) | | mΩ |
| t _{d(on)} | under following conditions: V _{CC} = 600V, I _c = 50A | | 90 | | ns |
| t _r | R _{Gon} = R _{Goff} = 15Ω, T _j = 125°C | | 55 | | ns |
| t _{d(off)} | V _{GE} = ± 15V | | 400 | | ns |
| t _f | | | 40 | | ns |
| E _{on(Eoff)} | | | 5.7(4.7) | | mJ |
| Inverse Diode under following conditions: | | | | | |
| V _F = V _{EC} | I _F = 50A; V _{GE} = 0V; T _j = 25(125)°C | | 2(1.8) | 2.5 | V |
| V _(TO) | T _j = 25(125)°C | | 1.1 | 1.2 | V |
| r _T | T _j = 25(125)°C | | 18 | 26 | mΩ |
| I _{RRM} | I _F = 50A; T _j = 125°C | | 80 | | A |
| Q _{rr} | di/dt = 2100A/us | | 8.5 | | uC |
| E _{rr} | V _{GE} = V | | 3.1 | | mJ |
| Thermal Characteristics | | | | | |
| R _{th(j-c)} | per IGBT | | | 0.3 | K/W |
| R _{th(j-c)D} | per Inverse Diode | | | 0.6 | K/W |
| R _{th(c-s)} | per module | | | 0.05 | K/W |
| Mechanical Data | | | | | |
| M _s | to heatsink M6 | 3 | | 5 | Nm |
| M _t | to terminals M5 | 2.5 | | 5 | Nm |
| w | | | | 160 | g |